

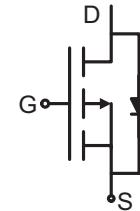
P-Channel Enhancement Mode Power MOSFET

Description

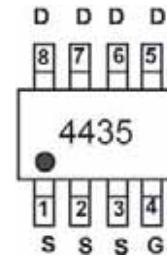
The RM4435 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V.

General Features

- $V_{DS} = -30V, I_D = -9.1A$
- $R_{DS(ON)} < 35m\Omega @ V_{GS}=-4.5V$
- $R_{DS(ON)} < 20m\Omega @ V_{GS}=-10V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package



Schematic diagram



Marking and pin assignment



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
4435	RM4435	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J = 150^\circ C$)	$I_C = 25^\circ C$	-11	A
	$T_C = 70^\circ C$	-9	
	$T_A = 25^\circ C$	-9.1	
	$T_A = 70^\circ C$	-7.2	
Drain Current-Pulsed ^(Note 1)	I_{DM}	-50	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	40	°C/W
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1	-1.5	-3	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-9.1\text{A}$	-	16	20	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-6.9\text{A}$	-	21	35	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-9.1\text{A}$	10	-	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	1600	-	PF
Output Capacitance	C_{oss}		-	350	-	PF
Reverse Transfer Capacitance	C_{rss}		-	300	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=-15\text{V}, I_{\text{D}}=-1\text{A}, V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=6\Omega$	-	10	-	nS
Turn-on Rise Time	t_r		-	15	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	110	-	nS
Turn-Off Fall Time	t_f		-	70	-	nS
Total Gate Charge	Q_g	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-9.1\text{A}$ $V_{\text{GS}}=-10\text{V}$	-	30	-	nC
Gate-Source Charge	Q_{gs}		-	5.5	-	nC
Gate-Drain Charge	Q_{gd}		-	8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-2.1\text{A}$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

RATING AND CHARACTERISTICS CURVES (RM4435)

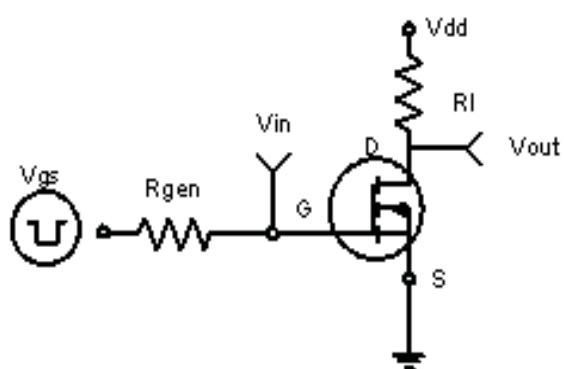


Figure 1:Switching Test Circuit

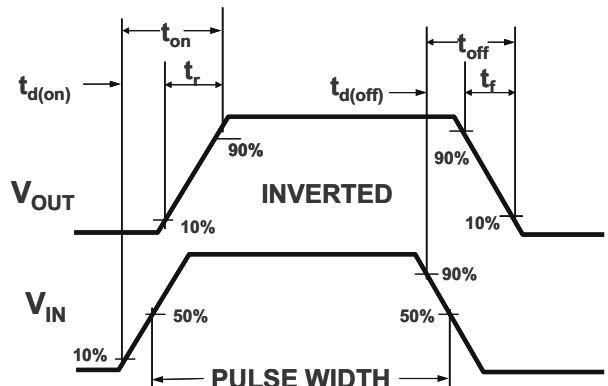


Figure 2:Switching Waveforms

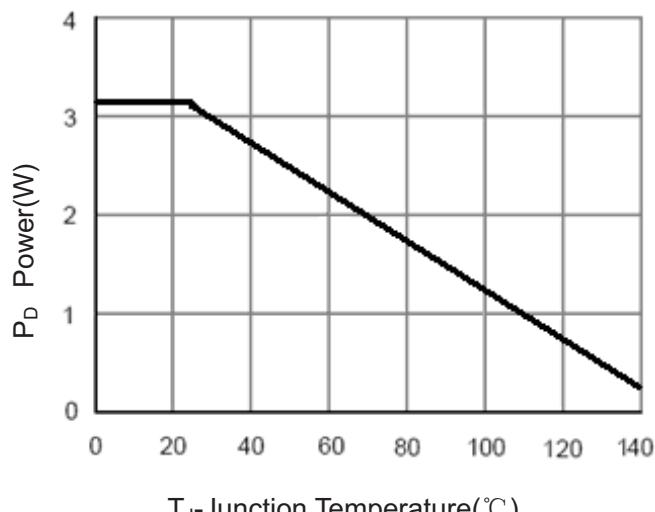


Figure 3 Power Dissipation

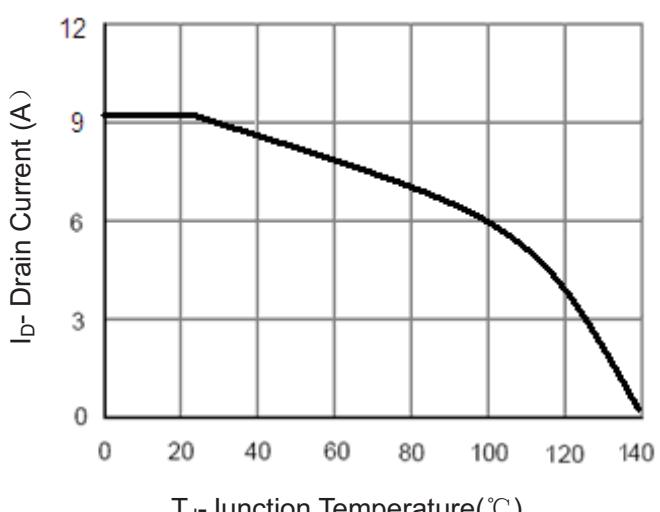


Figure 4 Drain Current

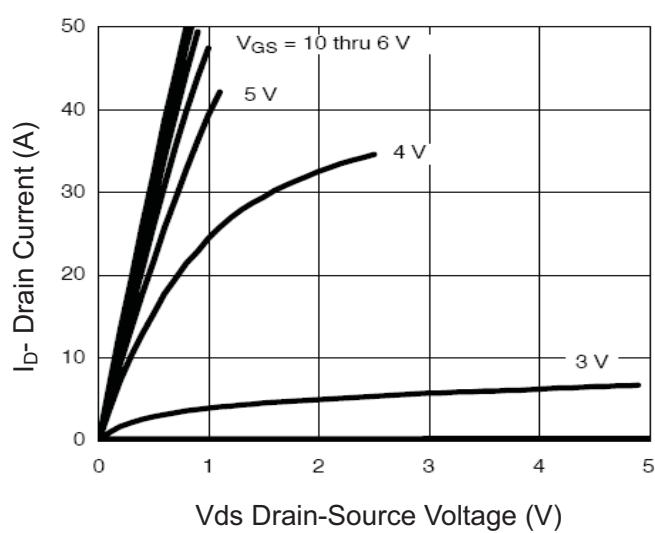


Figure 5 Output Characteristics

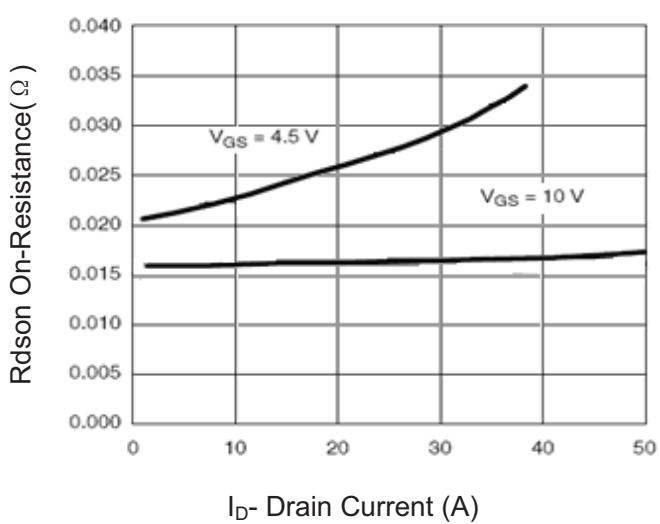


Figure 6 Drain-Source On-Resistance

RATING AND CHARACTERISTICS CURVES (RM4435)

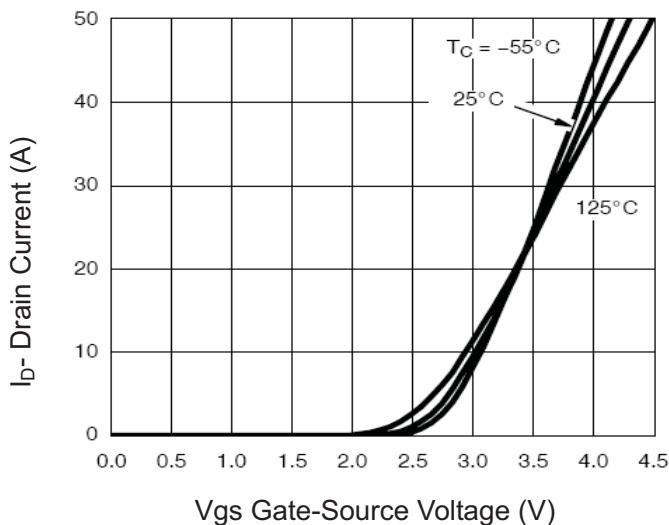


Figure 7 Transfer Characteristics

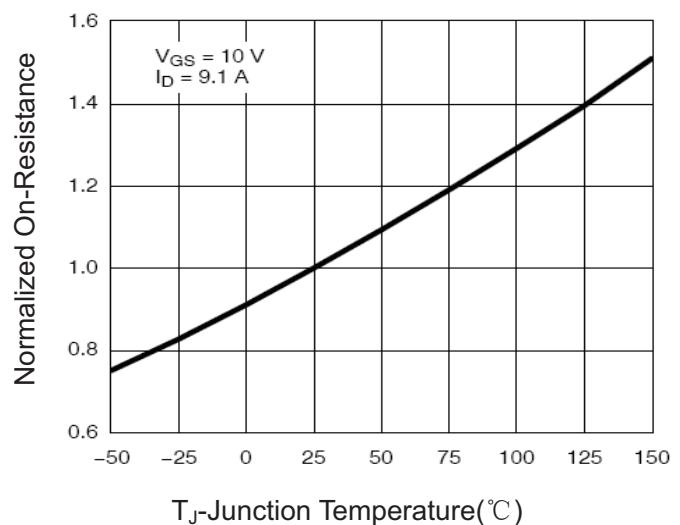


Figure 8 Drain-Source On-Resistance

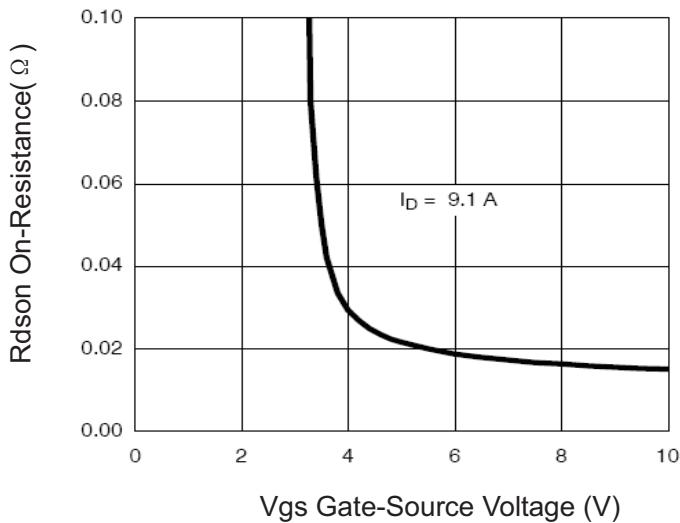


Figure 9 R_{DSON} vs V_{GS}

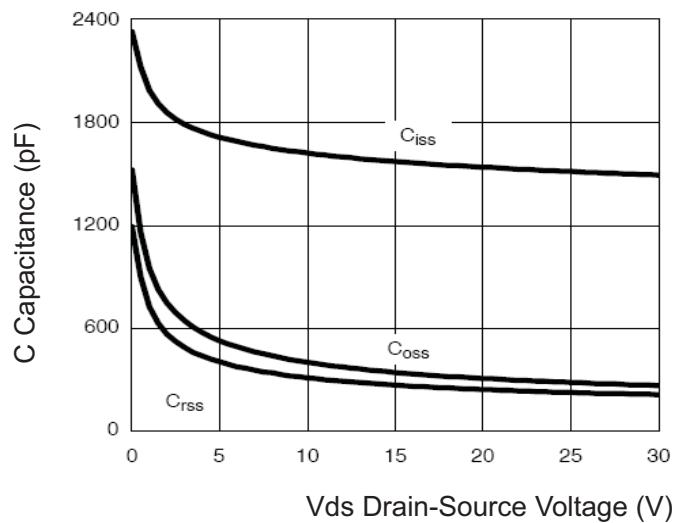


Figure 10 Capacitance vs V_{DS}

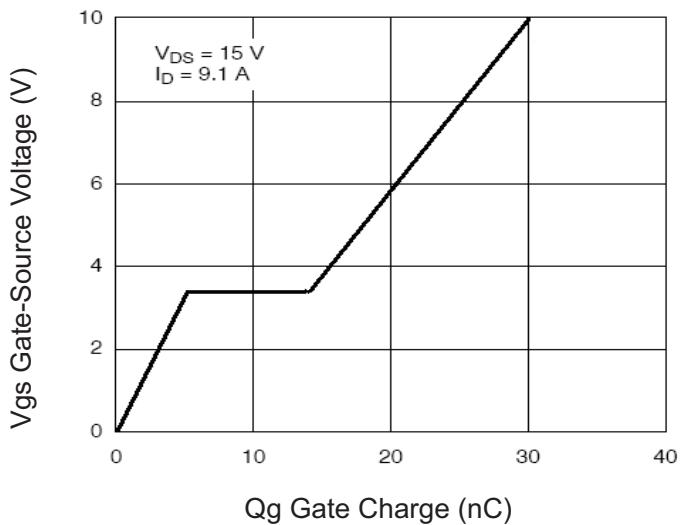


Figure 11 Gate Charge

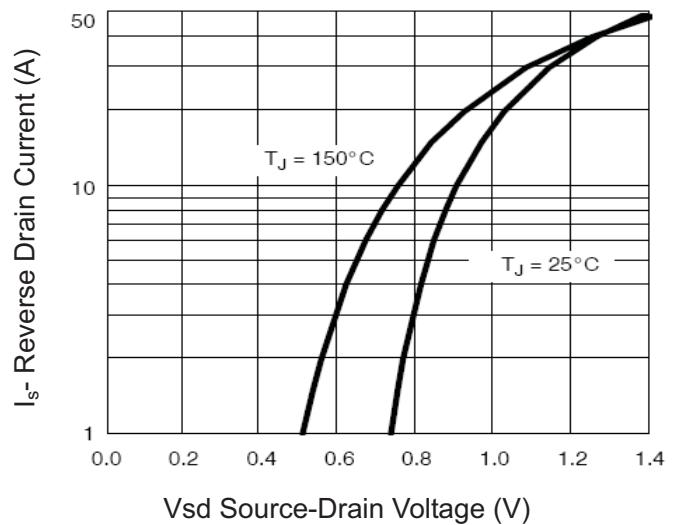


Figure 12 Source- Drain Diode Forward

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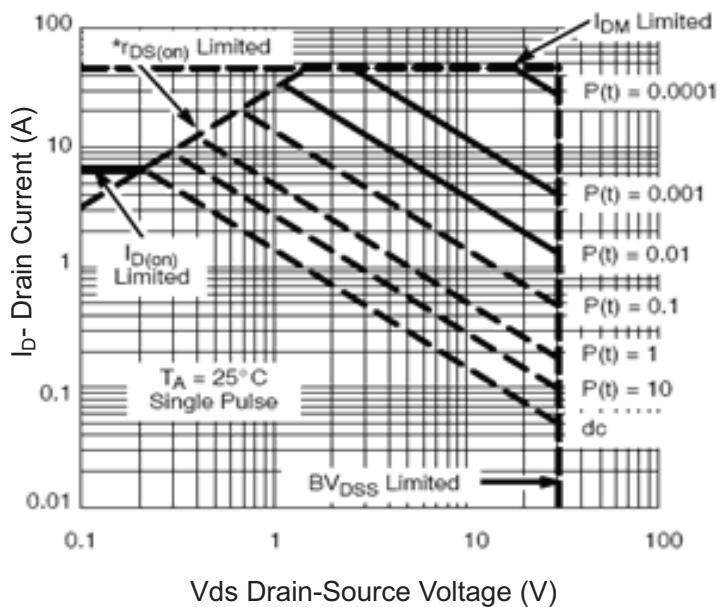


Figure 13 Safe Operation Area

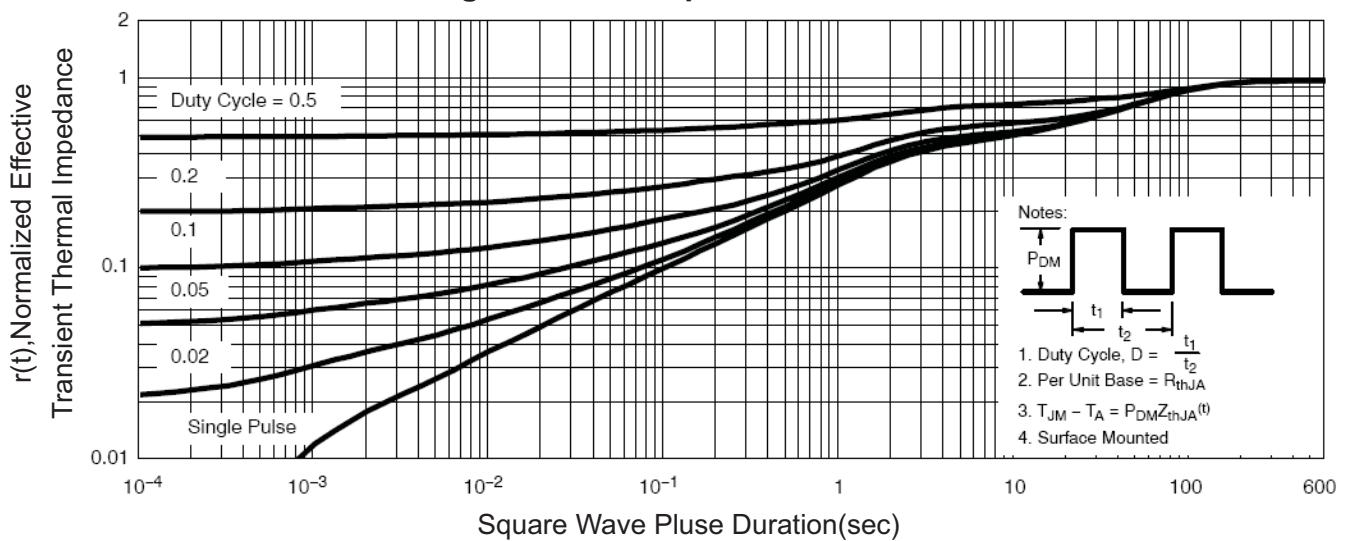
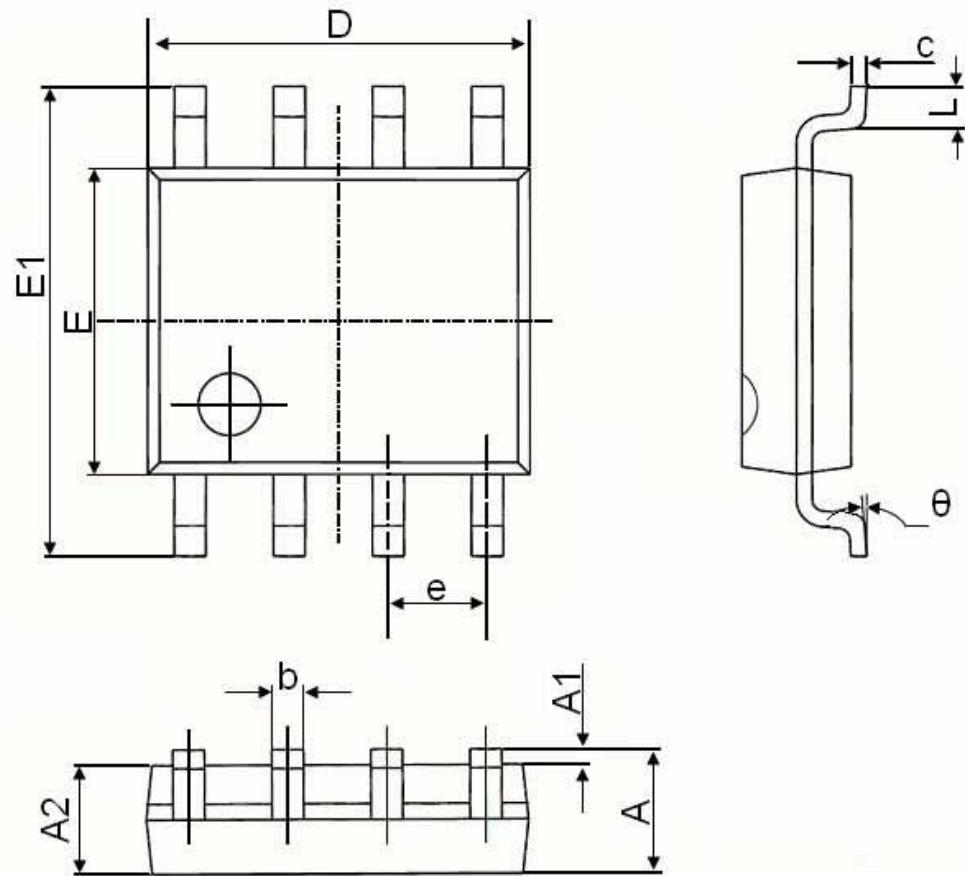


Figure 14 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0 °	8 °	0 °	8 °

Package	Tube (pcs/tube)	Tube (pcs/inner box)	Tube (pcs/cartoon)	Tape&Reel (pcs/reel)	Tape&Reel (pcs/inner box)	Tape&Reel (pcs/cartoon)
DFN5x6/DFN3x3	100	10,000	100,000	2,500	5,000	40,000
DFN1006	—	—	—	10,000	10,000	400,000
SOP-8	100	10,000	100,000	4,000	4,000	20,000
TSSOP-8	100	32,000	128,000	3,000	6,000	48,000
SOT-23-3L	—	—	—	3,000	30,000	120,000
SOT-23-6L	—	—	—	3,000	30,000	120,000
SOT-23(6R)	—	—	—	3,000	30,000	120,000
SOT-363	—	—	—	3,000	30,000	120,000
SOT-523	—	—	—	3,000	30,000	120,000
SOT223	—	—	—	2,500	2,500	20,000
TO-220	50	1,000	5,000	—	—	—
TO-220F	50	1,000	10,000	—	—	—
TO-247	30	300	1,200	—	—	—
TO-251	80	4,000	40,000	—	—	—
TO-251S(4R)	80	4,000	40,000	—	—	—
TO-252-2L(4R)	80	4,000	40,000	2,500	2,500	25,000
TO-263-2L	50	1,000	10,000	800	800	8,000
TO-3P	30	300	3,000	—	—	—
TO-92	—	—	—	1,000(袋装)	10,000	100,000

Revise History